

**DESCRIPTION** The 2SC945 is designed for use in driver stage of AF amplifier and low speed switching.

**FEATURES**

- High Voltage LV<sub>CEO</sub> : 50 V MIN.
- Excellent  $h_{FE}$  Linearity

$h_{FE1}$  (0.1 mA)/ $h_{FE2}$  (1.0 mA) : 0.92 TYP.

**ABSOLUTE MAXIMUM RATINGS**

Maximum Temperatures

Storage Temperature ..... -55 to +125 °C

Junction Temperature ..... +125 °C Maximum

Maximum Power Dissipation (Ta = 25 °C)

Total Power Dissipation ..... 250 mW

Maximum Voltages and Currents (Ta = 25 °C)

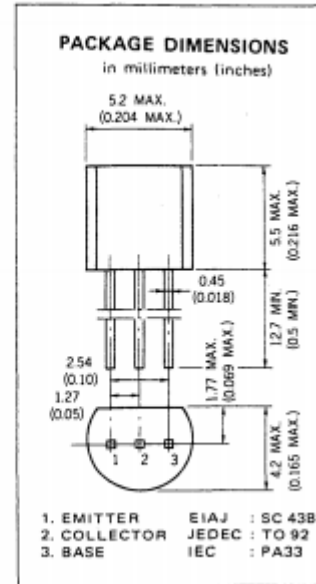
V<sub>CBO</sub> Collector to Base Voltage ..... 60 V

V<sub>CEO</sub> Collector to Emitter Voltage ..... 50 V

V<sub>EBO</sub> Emitter to Base Voltage ..... 5.0 V

I<sub>C</sub> Collector Current ..... 100 mA

I<sub>B</sub> Base Current ..... 20 mA



**ELECTRICAL CHARACTERISTICS (Ta = 25 °C)**

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
$h_{FE1}$	DC Current Gain	50	185			V <sub>CE</sub> = 6.0 V, I <sub>C</sub> = 0.1 mA
$h_{FE2}$	DC Current Gain	90	200	600		V <sub>CE</sub> = 6.0 V, I <sub>C</sub> = 1.0 mA
NF	Noise Figure		0.8	15	dB	V <sub>CE</sub> = 6.0 V, I <sub>C</sub> = 0.1 mA, R <sub>G</sub> = 2.0 kΩ, f = 1.0 kHz
f <sub>T</sub>	Gain Bandwidth Product	150	250	450	MHz	V <sub>CE</sub> = 6.0 V, I <sub>E</sub> = -10 mA
C <sub>cb</sub>	Collector to Base Capacitance		3.0	4.0	pF	V <sub>CB</sub> = 6.0 V, I <sub>E</sub> = 0, f = 1.0 MHz
I <sub>CBO</sub>	Collector Cutoff Current			100	nA	V <sub>CB</sub> = 60 V, I <sub>E</sub> = 0
I <sub>EBO</sub>	Emitter Cutoff Current			100	nA	V <sub>EB</sub> = 5.0 V, I <sub>C</sub> = 0
V <sub>BE</sub>	Base to Emitter Voltage	0.55	0.62	0.65	V	V <sub>CE</sub> = 6.0 V, I <sub>C</sub> = 1.0 mA
V <sub>CE(sat)</sub>	Collector Saturation Voltage		0.15	0.3	V	I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA
V <sub>BE(sat)</sub>	Base Saturation Voltage		0.86	1.0	V	I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA

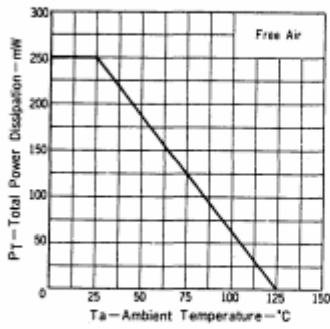
**Classification of  $h_{FE2}$**

Rank	R	Q	P	K
Range	90 - 180	135 - 270	200 - 400	300 - 600

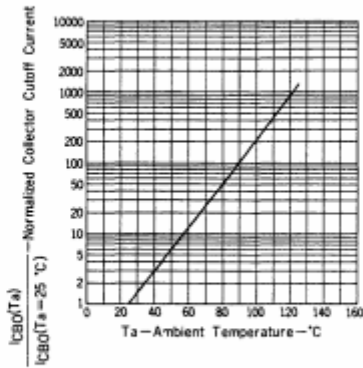
$h_{FE2}$  Test Conditions : V<sub>CE</sub> = 6.0 V, I<sub>C</sub> = 1.0 mA

TYPICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$  unless otherwise noted)

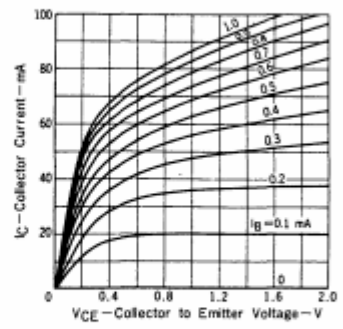
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



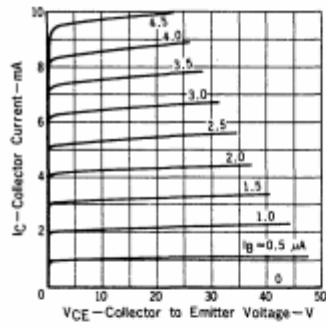
NORMALIZED COLLECTOR CUTOFF CURRENT vs. AMBIENT TEMPERATURE



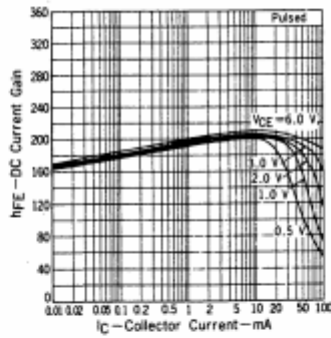
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



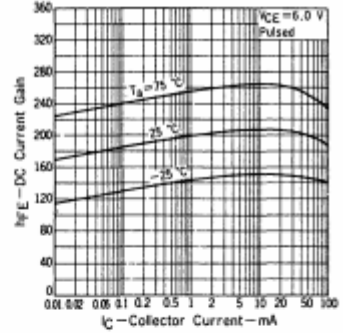
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



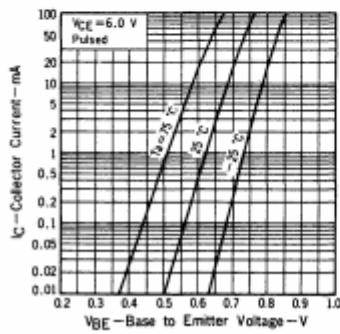
DC CURRENT GAIN vs. COLLECTOR CURRENT



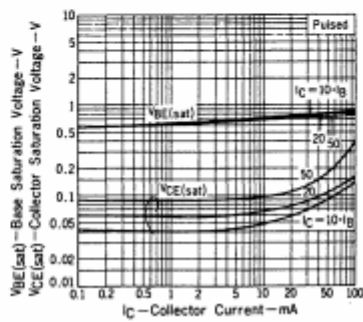
DC CURRENT GAIN vs. COLLECTOR CURRENT



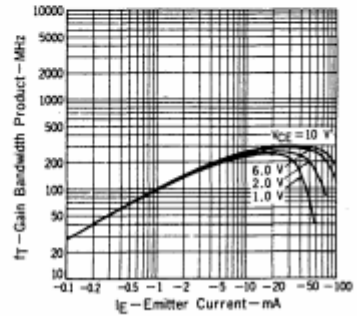
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



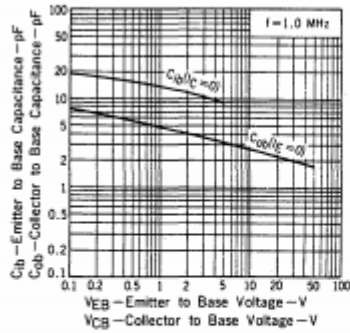
COLLECTOR AND BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



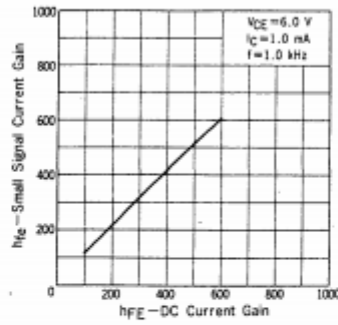
GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



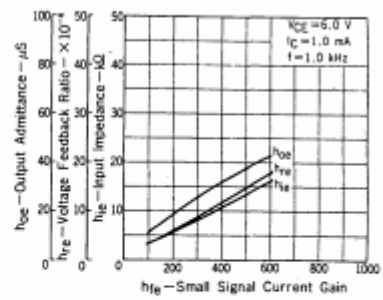
**EMITTER TO BASE AND COLLECTOR TO BASE CAPACITANCE vs. REVERSE VOLTAGE**



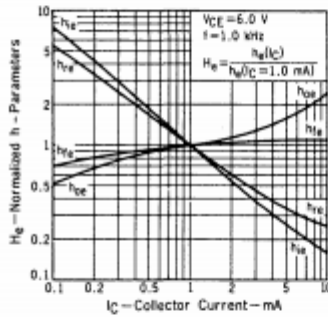
**SMALL SIGNAL CURRENT GAIN vs. DC CURRENT GAIN**



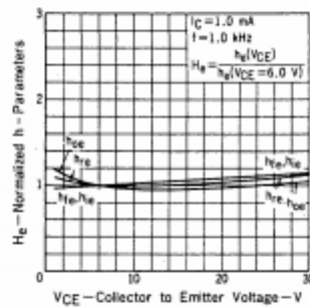
**INPUT IMPEDANCE, VOLTAGE FEEDBACK RATIO AND OUTPUT ADMITTANCE vs. SMALL SIGNAL CURRENT GAIN**



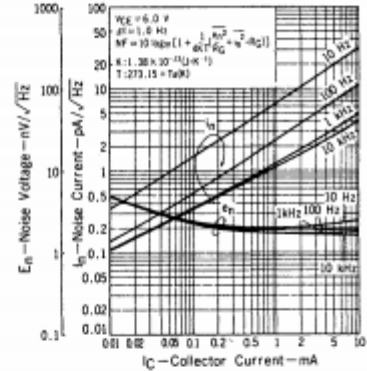
**NORMALIZED h-PARAMETERS vs. COLLECTOR CURRENT**



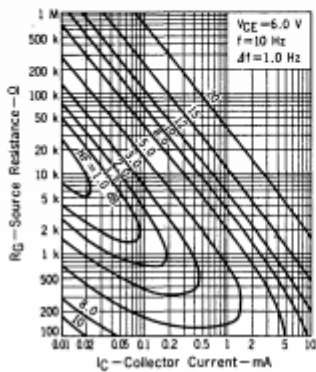
**NORMALIZED h-PARAMETERS vs. COLLECTOR TO EMITTER VOLTAGE**



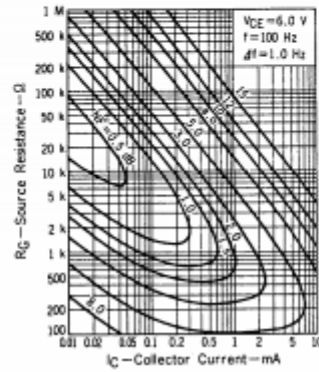
**En AND In vs. COLLECTOR CURRENT**



**NOISE FIGURE MAP 1**



**NOISE FIGURE MAP 2**



**NOISE FIGURE MAP 3**

